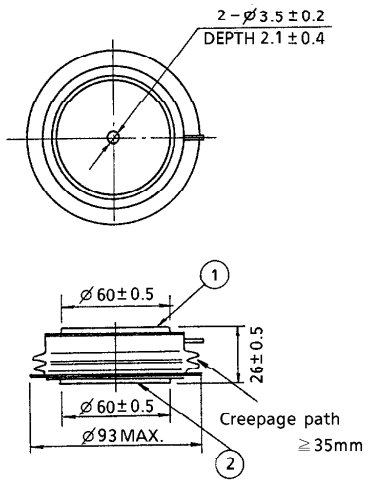
TENTATIVE TOSHIBA FAST RECOVERY DIODE SILICON DIFFUSED TYPE

800JXH23

HIGH SPEED RECTIFIER APPLICATIONS

Unit in mm

- Repetitive Peak Reverse Voltage : V_{RRM} = 6000V
- Average Forward Current : $I_{F(AV)}$ = 800A
- Double Side Cooling



1. CATHODE
2. ANODE

JEDEC	—
EIAJ	—
TOSHIBA	3-93B1A

Weight : 800g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	6000	V
Non-Repetitive Peak Reverse Voltage (Non-Repetitive ≦ 5ms, T_j ≦ 0~125°C)	V_{RSM}	6300	V
Average Forward Current	$I_{F(AV)}$	800	A
Peak One Cycle Surge Forward Current (Non-Repetitive, 10ms Width Half Sine Waveform)	I_{FSM}	16000	A
Junction Temperature Range	T_j	−40~125	°C
Storage Temperature Range	T_{stg}	−40~150	°C
Mounting Force	—	29.4 ± 9.8	kN

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Repetitive Peak Reverse Current	I_{RRM}	V_{RRM} = 6000V, T_j = 125°C	—	—	100	mA
Peak Forward Voltage	V_{FM}	I_{FM} = 2500A, T_j = 125°C	—	5.0	—	V
Reverse Recovery Charge	Q_{rr}	I_F = 800A, T_j = 125°C di_F/dt = 100A/μs	—	1800	—	μC
Thermal Resistance	$R_{th(j-f)}$	DC	—	—	0.014	°C/W

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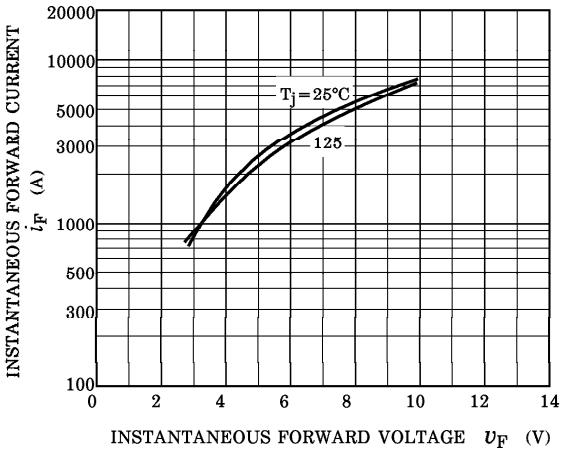
$i_F - v_F$ (TYP.)



t_{rr}, I_{rr} – di_F/dt (TYP.)